

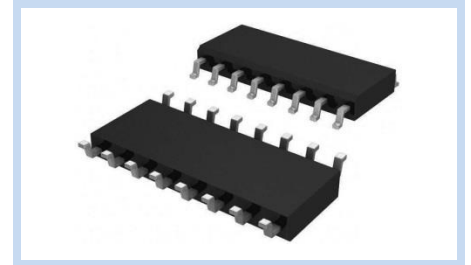
ESD Suppressor 12V 8-Bidirectional SOIC-16

ME128B20SO16

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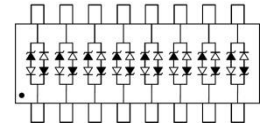
FEATURE

- IEC 61000-4-2 ESD: $\pm 30\text{KV}$ (Air) $\pm 30\text{KV}$ (Contact)
- ESD Protection for eight Bidirectional Channels
- Low Leakage Current
- Low Capacitance and Clamping Voltage
- Solid-State Silicon-Avalanche Technology



APPLICATION

- Wireless Communication Circuit
- WAN Equipment
- CSU/DSU
- Multi Plexers
- Routers
- ISP Equipment



MAXIMUM RATINGS AND CHARACTERISTICS

Parameter	Symbol	Value	Unit
ESD Voltage (Contact discharge)	V_{ESD}	± 30	KV
ESD Voltage (Air discharge)		± 30	
Peak Pulse Power($t_p=8/20\mu s$)	P_{PP}	500	W
Operating & Storage Temperature Range	T_J, T_{STG}	$-55\sim+150$	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS

Parameter	Condition	Symbol	Min.	Typ.	Max.	Unit
Reverse Stand-Off Voltage	--	V_{RWM}	--	--	12	V
Reverse Breakdown Voltage	$I_{BR}=1\text{mA}$	V_{BR}	13.4	--	--	V
Reverse Leakage Current	$V_R=12\text{V}$, Each I/O Pin	I_R	--	--	1	μA
Clamping Voltage	$I_{PP}=1\text{A}$, $t_p=8/20\mu s$	V_C	--	--	20	V
	$I_{PP}=10\text{A}$, $t_p=8/20\mu s$		--	--	28	
Off State Junction Capacitance	$V_{dc}=0$, $f=1\text{MHz}$, Between I/O pins and GND	C_J	--	--	3	pF

Notes: $T_J=25^{\circ}\text{C}$ unless otherwise specified

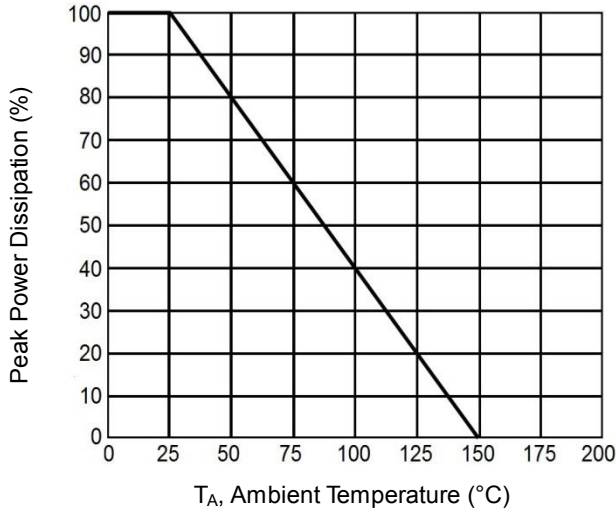
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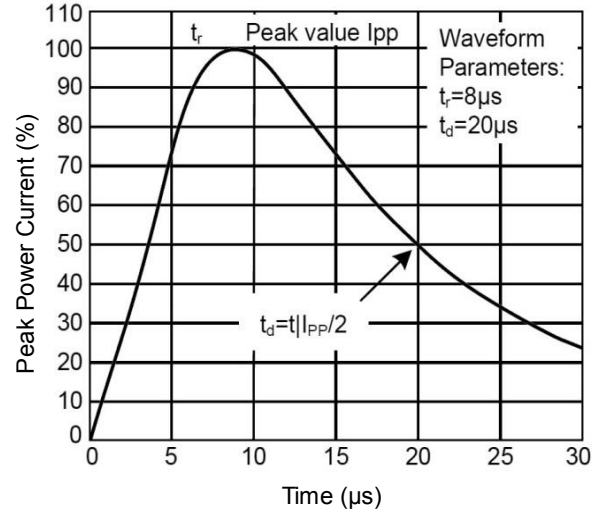
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CHARACTERISTIC CURVES

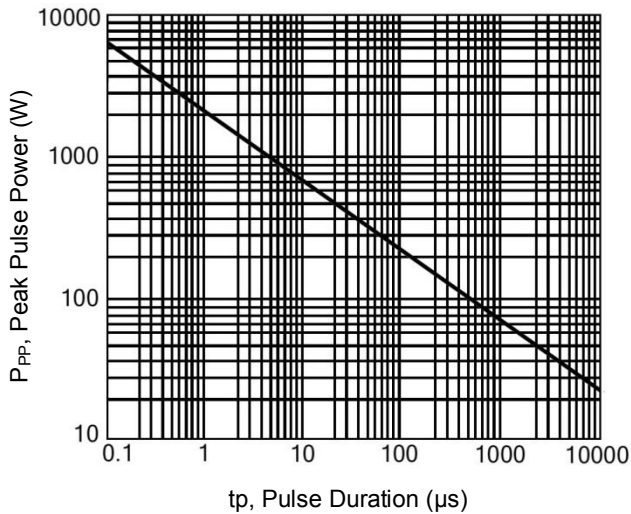
Derating Curve



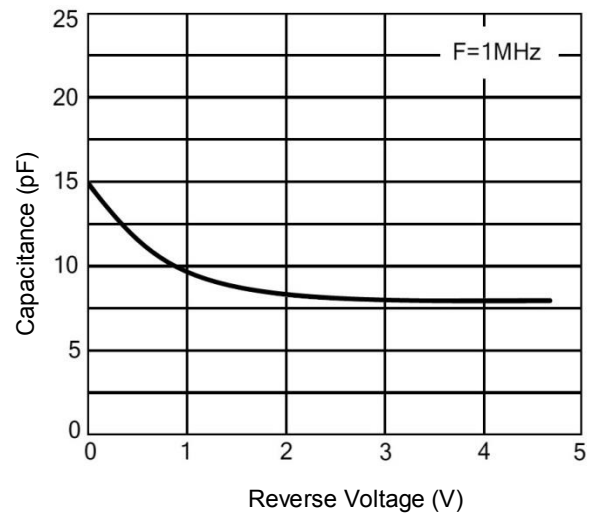
Pulse Waveforms



Non-Repetitive Peak Pulse vs. Pulse Time



Capacitance vs. Reverse Voltage



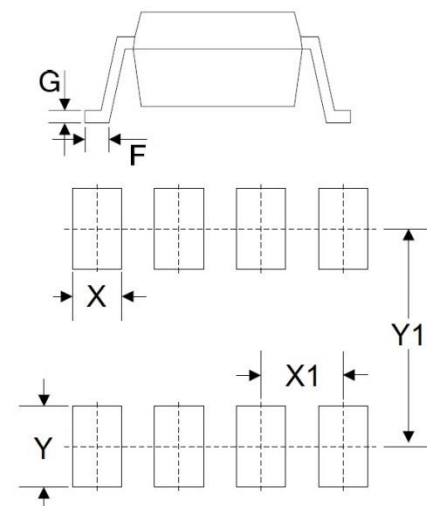
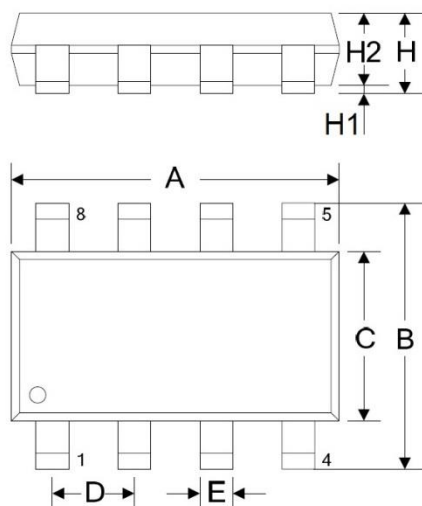
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DIMENSIONS AND RECOMMENDED LAND PATTERN

Item	Min (mm)	Max (mm)
A	4.80	5.00
B	5.80	6.20
C	3.80	4.00
D	1.27	1.27
E	0.33	0.51
F	0.40	1.27
G	0.19	0.25
H	1.35	1.75
H1	0.10	0.25
H2	1.45	1.45
X	0.73	0.73
X1	1.27	1.27
Y	1.20	1.20
Y1	6.60	6.60



*Specifications subject to change without notice.